IN THE SPECIFICATION:

[0035] (Amended) The radiation system may include a source LA (e.g. an Hg lamp, an excimer laser, a laser-produced plasma source, a discharge plasma source or an undulator or wiggler provided around the path of an electron beam in a storage ring or synchrotron) which produces a beam of UV or EUV radiation. This beam is caused to traverse either directly or after being passed through conditioning means, such as a beam expander Ex, various optical components comprised in the illumination system IL – e.g. beam shaping optics, adjusting means AM, an integrator IN and a condenser CO – also included in the radiation system so that the resultant beam PB has a desired shape and intensity distribution in its cross section.

[0036] (Amended) The beam PB subsequently intercepts the mask MA which is held on a mask table MT. Having been selectively reflected by the mask MA, the beam PB traverses the lens PL, which focuses the beam PB onto an exposure area C of the substrate W. With the aid of the interferometric displacement measuring means IF, the substrate table WT can be moved accurately by the second positioning means PW, e.g. so as to position different exposure areas C in the path of the beam PB using wafer alignment marks P1, P2. Similarly, the first positioning means PM can be used to accurately position the mask MA using mask alignment marks M1, M2 with respect to the path of the beam PB. In general, movement of the object tables MT, WT relative to a base plate BP will be realized with the aid of a long-stroke module (course positioning) and a short-stroke module (fine positioning), which are not explicitly depicted in Figure 1. In the case of a waferstepper (as opposed to a step-and-scan apparatus) the mask table may be connected only to a short-stroke positioning device, to make fine adjustments in mask orientation and position, or it may simply be fixed.